

Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (tp = 8/20μs)	P_{pk}	135	Watts
Peak Pulse Current (tp = 8/20µs) ¹	I _{PP}	15	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	+/-30 +/-25	kV
Operating Temperature	T _J	-55 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Note: 1) Any I/O to GND

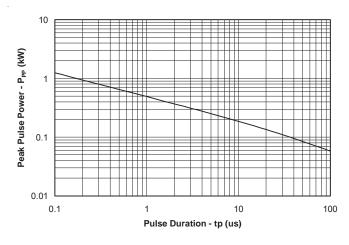
Electrical Characteristics (T=25°C)

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V _{RWM}				2.5	V
Punch-Through Voltage	V _{PT}	I _{PT} = 2μA Any I/O to GND	2.7			V
Snap-Back Voltage	V _{SB}	I _{SB} = 50mA Any I/O to GND	2.0			V
Reverse Leakage Current	I _R	V _{RWM} = 2.5V, T=25°C Any I/O to GND			0.5	μΑ
Clamping Voltage	V _c	I _{PP} = 1A, t _p = 8/20μs Any I/O to GND			4.8	V
Clamping Voltage	V _c	I _{PP} = 10A, t _p = 8/20μs Any I/O to GND			7.7	V
Clamping Voltage	V _c	I _{PP} = 15A, t _p = 8/20μs Any I/O to GND			9.0	V
Forward Voltage	V _F	I _{PP} = 10A, t _p = 8/20μs GND to Any I/0			3.5	V
Forward Voltage	V _F	I _{PP} = 15A, t _p = 8/20μs GND to Any I/0			4.8	V
Junction Capacitance	C _j	Between I/O pins and Ground $V_R = 0V - 2.5V$, $f = 1MHz$			5	pF
		Between I/O pins $V_R = 0V - 2.5V$, $f = 1MHz$		2.0		pF

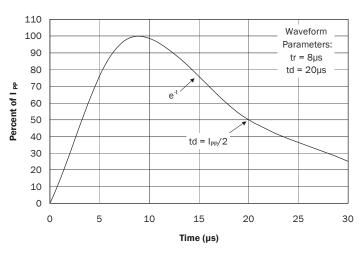


Typical Characteristics

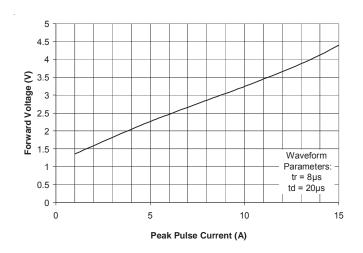
Non-Repetitive Peak Pulse Power vs. Pulse Time



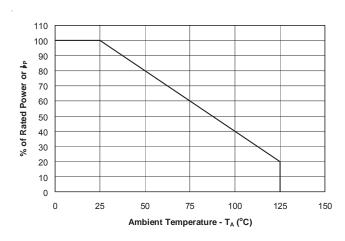
Surge Current Output Waveform (tp = 8/20us)



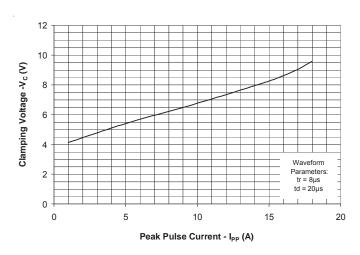
Froward Voltage vs. Peak Pulse Current GND to any I/O (tp = 8/20us)



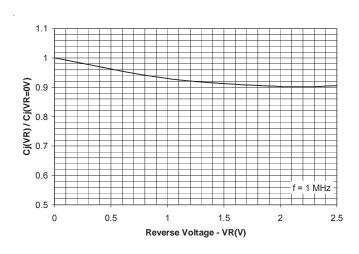
Power Derating Curve



Clamping Voltage vs. Peak Pulse Current Any I/O to GND (tp = 8/20us)



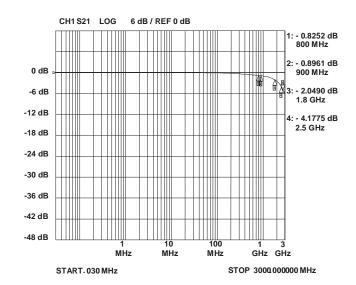
Normalized Capacitance vs. Reverse Voltage (Any I/O to GND)



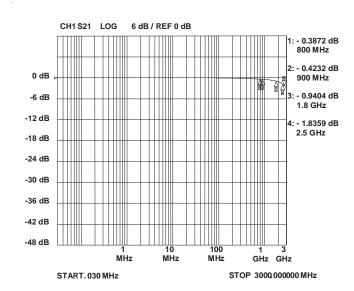


Typical Characteristics

Insertion Loss S21 (I/O to Gnd)



Insertion Loss S21 (I/O to I/O)





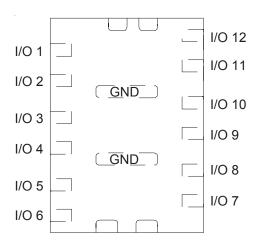
Applications Information

Device Connection Options for Protection of Twelve High-Speed Data Lines

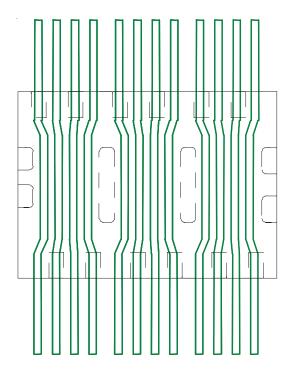
This device is designed to protect up to twelve high-speed data lines. It has been optimized for use on LVDS interfaces. The RClamp7512N is constructed using Semtech's proprietary EPD process technology. The EPD process provides low stand-off (turn-on) voltages with significant reductions while maintaining good clamping characteristics and high surge capability. They feature a true operating voltage of 2.5 volts. The characteristics of the RClamp7512N eliminate the need to add an external resistor for protection of LVDS interfaces.

Each pin (1-12) is internally connected to a protection circuit. The pins are slightly staggered to allow clearance for routing traces up to 0.100mm wide with 0.150mm spacing between traces. This flow through design means that the RClamp7512N can be used on PC boards with as few as 2-layers. The device also features two center ground tabs. These pads provide a low inductance path for the surge current to ground. The low inductance ground path is especially critical for reducing the clamping voltage during ESD events.

Pin Configuration (Top View)

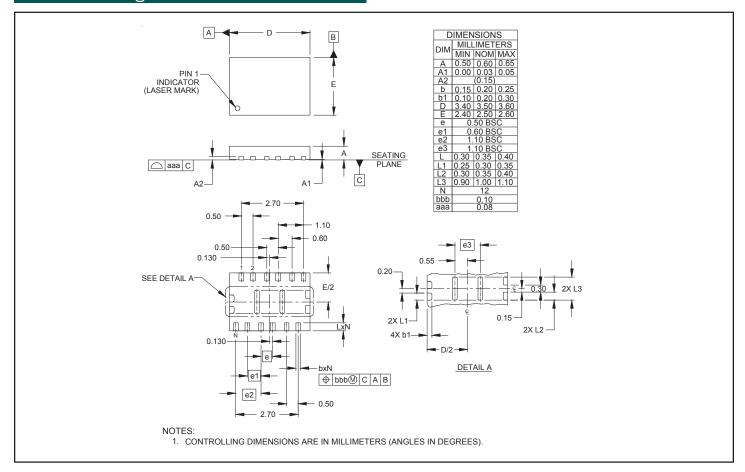


Layout Example

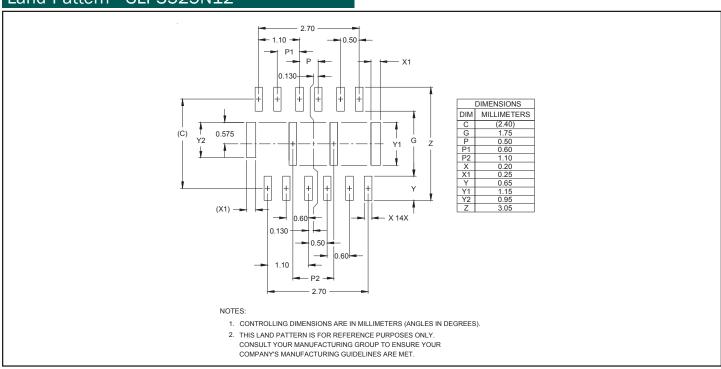




Outline Drawing - SLP3525N12

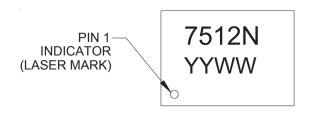


Land Pattern - SLP3525N12





Marking



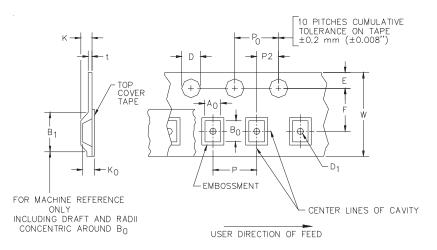
Ordering Information

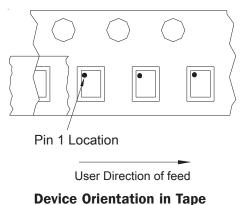
Part Number	Lead Finish	Qty per Reel	Reel Size	
RClamp7512N.TCT	NiPdAu	3000	7 Inch	

RailClamp and RClamp are marks of Semtech Corporation

YYWW = Date Code

Tape and Reel Specification





A0	ВО	ко		
2.80 +/-0.20 mm	3.80 +/-0.20 mm	0.80 +/-0.10 mm		

Tape Width	B, (Max)	D	D1	E	F	K (MAX)	Р	PO	P2	T(MAX)	W
12 mm	8.2 mm	1.5 + 0.1 mm - 0.0 mm)	0.5 mm ±0.05	1.750±.10 mm	5.5±0.05 mm	4.5 mm	8.0±0.1 mm	4.0±0.1 mm	2.0±0.05 mm	0.4 mm	12.0 mm ± 0.3 mm

Contact Information

Semtech Corporation Protection Products Division 200 Flynn Rd., Camarillo, CA 93012 Phone: (805)498-2111 FAX (805)498-3804

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Semtech:

RCLAMP7512N.TCT